

EMC-OPTIMIZED CAN TRANSCEIVER

Check for Samples: SN65HVD1050-Q1

FEATURES

- **Qualified for Automotive Applications**
- **Customer-Specific Configuration Control Can** Be Supported Along With Major-Change **Approval**
- Improved Drop-In Replacement for TJA1050
- Meets or Exceeds the Requirements of ISO 11898-2
- **GIFT/ICT Compliant**
- ESD Protection up to ±8 kV (Human-Body Model) on Bus Pins
- **High Electromagnetic Immunity (EMI)**
- Low Electromagnetic Emissions (EME)
- Bus-Fault Protection of -27 V to 40 V
- **Dominant Time-Out Function**
- **Thermal Shutdown Protection**
- Power-Up/Down Glitch-Free Bus Inputs and **Outputs**
 - High Input Impedance With Low V_{CC}
 - Monotonic Outputs During Power Cycling

APPLICATIONS

- **GMW3122 Dual-Wire CAN Physical Layer**
- SAE J2284 High-Speed CAN for Automotive **Applications**
- SAE J1939 Standard Data Bus Interface
- ISO 11783 Standard Data Bus Interface
- NMEA 2000 Standard Data Bus Interface
- **Industrial Automation**
 - DeviceNet™ Data Buses (Vendor ID #806)

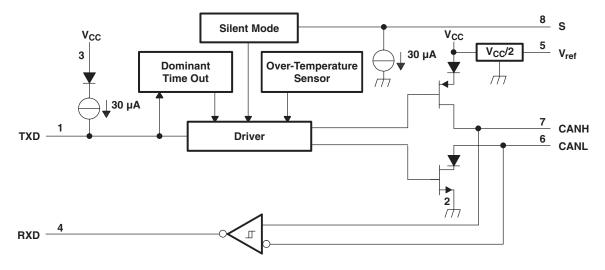
DESCRIPTION

SN65HVD1050 The meets or exceeds specifications of the ISO 11898 standard for use in applications employing a Controller Area Network (CAN). The device is qualified for use in automotive applications.

As a CAN transceiver, this device provides differential transmit capability to the bus and differential receive capability to a CAN controller at signaling rates up to 1 megabit per second (Mbps)(1).

(1) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

FUNCTION BLOCK DIAGRAM



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. DeviceNet is a trademark of Texas Instruments.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

DESCRIPTION (CONTINUED)

Designed for operation is especially harsh environments, the SN65HVD1050 features cross-wire, over-voltage, and loss of ground protection from –27 V to 40 V, over-temperature protection, a –12-V to 12-V common-mode range, and withstands voltage transients from –200 V to 200 V according to ISO 7637.

Pin 8 provides for two different modes of operation: high-speed or silent mode. The high-speed mode of operation is selected by connecting S (pin 8) to ground.

If a high logic level is applied to the S pin of the SN65HVD1050, the device enters a listen-only silent mode during which the driver is switched off while the receiver remains fully functional.

In silent mode, all bus activity is passed by the receiver output to the local protocol controller. When data transmission is required, the local protocol controller reverses this low-current silent mode by placing a logic low on the S pin to resume full operation.

A dominant time-out circuit in the SN65HVD1050 prevents the driver from blocking network communication with a hardware or software failure. The time-out circuit is triggered by a falling edge on TXD (pin 1). If no rising edge is seen before the time-out constant of the circuit expires, the driver is disabled. The circuit is then reset by the next rising edge on TXD.

 V_{ref} (pin 5) is available as a $V_{CC}/2$ voltage reference.

The SN65HVD1050 is characterized for operation from -40°C to 125°C.

ORDERING INFORMATION(1)

| PART NUMBER | PACKAGE ⁽²⁾ | MARKED AS | ORDERING NUMBER |
|----------------|------------------------|--------------|-------------------------|
| SN65HVD1050-Q1 | SOIC-8 | H1050Q | SN65HVD1050QDRQ1 (reel) |

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

Application Hint: CAN Nodes Using Common-Mode Chokes

The SN65HVD1050 has been EMC optimized to allow use in CAN systems without a common-mode choke. However, sometimes the CAN network and termination architecture may require their use. If a common-mode choke is used in a CAN node where bus-line shorts to dc voltages may be possible, care should be taken in the choice of common-mode choke (winding type, core type, and value) along with the termination and protection scheme of the node and bus. During CAN bus shorts to dc voltages the inductance of the common-mode choke may cause inductive flyback transients. Some combinations of common-mode chokes, bus termination, and shorting voltages take the bus voltages outside the absolute maximum ratings of the device, possibly leading to damage.

⁽²⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

| | | UNIT |
|----------------|---|-----------------|
| V_{CC} | Supply voltage range (2) | -0.3 V to 6 V |
| | Voltage range at any bus terminal (CANH, CANL, V _{ref}) | –27 V to 40 V |
| Io | Receiver output current | 20 mA |
| V_{I} | Voltage input range, ac transient pulse (3) (CANH, CANL) | –200 V to 200 V |
| V_{I} | Voltage input range (TXD, S) | -0.3 V to 6 V |
| T_J | Junction temperature range | -40°C to 170°C |
| T _A | Operating free-air temperature range | -40°C to 125°C |

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

ELECTROSTATIC DISCHARGE PROTECTION

over operating free-air temperature range (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | |
|-----------------------------|--------------------------|-----------------------|---------|
| | Human-Body Model (2) | Bus terminals and GND | ±8 kV |
| | Human-body Woder | All pins | ±4 kV |
| Electrostatic discharge (1) | Charged-Device Model (3) | All pins | ±1.5 kV |
| | Machine Model | | ±200 V |

- (1) All typical values at 25°C.
- (2) Tested in accordance JEDEC Standard 22, Test Method A114-A.
- (3) Tested in accordance JEDEC Standard 22, Test Method C101.

RECOMMENDED OPERATING CONDITIONS

| | | | MIN | MAX | UNIT |
|-----------------------------------|---|---|------|------|------|
| V _{CC} | Supply voltage | | 4.75 | 5.25 | V |
| V _I or V _{IC} | Voltage at any bus terminal (separately or common mode) | Voltage at any bus terminal (separately or common mode) | | 12 | V |
| V _{IH} | High-level input voltage | TXD, S | 2 | 5.25 | V |
| V _{IL} | Low-level input voltage | TXD, S | 0 | 0.8 | V |
| V_{ID} | Differential input voltage | • | -6 | 6 | V |
| | High level autout august | Driver | | | A |
| ІОН | High-level output current | Receiver | -2 | | mA |
| | Lauria autoritario | Driver | | 70 | A |
| I _{OL} | Low-level output current | Receiver | | 2 | mA |
| TJ | Junction temperature | See Thermal Characteristics table | | 150 | °C |

SUPPLY CURRENT

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAM | ETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|--------------------|-------------|--|-----|-----|-----|--------|
| | | Silent mode | S at V _{CC} , V _I = V _{CC} | | 6 | 10 | |
| I _{CC} | 5-V supply current | Dominant | $V_I = 0 \text{ V}, 60-\Omega \text{ load}, \text{ S at } 0 \text{ V}$ | | 50 | 70 | mA |
| | | Recessive | V _I = V _{CC} , No load, S at 0 V | | 6 | 10 | - |

⁽³⁾ Tested in accordance with ISO 7637-1, test pulses 1, 2, 3a, 3b, 5, 6, and 7. ISO 7637-1 transient tests are ac only; if dc may be coupled in with ac transients, externally protect the bus pins within the absolute maximum voltage range at any bus terminal (–27 V to 40 V). If common-mode chokes are used in the system and the bus lines may be shorted to dc, ensure that the choke type and value in combination with the node termination and shorting voltage either will not create inductive flyback outside of voltage maximum specification or use an external transient-suppression circuit to protect the transceiver from the inductive transients



DEVICE SWITCHING CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

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|-----------------------|--|--|-----|-----|------|
| | PARAMETER | TEST CONDITIONS | MIN | MAX | UNIT |
| t _{d(LOOP1)} | Total loop delay, driver input to receiver output, recessive to dominant | S at 0 V, See Figure 9 | 90 | 230 | ns |
| $t_{d(LOOP2)}$ | Total loop delay, driver input to receiver output, dominant to recessive | S at 0 V, See Figure 9 | 90 | 230 | ns |

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | | TEST CONDITIONS | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|---|--|---|---|-------------|--------------------|-------|------|
| V | Bus output voltage (dominant) | CANH | $V_I = 0 \text{ V}, \text{ S at } 0 \text{ V}, \text{ R}_L = 60 \Omega, \text{ See Figure 1}$ | 2.9 | 3.4 | 4.5 | V |
| $V_{O(D)}$ | Bus output voltage (dominant) | CANL | and Figure 2 | | | 1.5 | V |
| $V_{O(R)}$ | Bus output voltage (recessive) | | V_I = 3 V, S at 0 V, R_L = 60 Ω , See Figure 1 and Figure 2 | 2 | 2.3 | 3 | ٧ |
| V Differential and and trailing of (decrined) | | V_I = 0 V, R_L = 60 Ω , S at 0 V, See Figure 1, Figure 2, and Figure 3 | 1.5 | | 3 | ٧ | |
| $V_{OD(D)}$ | Differential output voltage (dominant) | | V_I = 0 V, R_L = 45 Ω , S at 0 V, See Figure 1, Figure 2, and Figure 3 | 1.4 | | 3 | ٧ |
| V | Differential output valtage (rece | $V_I = 3 \text{ V}$, S at 0 V, See Figur | V _I = 3 V, S at 0 V, See Figure 1 and Figure 2 - V _I = 3 V, S at 0 V, No Load | | | 0.012 | V |
| $V_{OD(R)}$ | Differential output voltage (rece | ssive) | | | | 0.05 | V |
| $V_{OC(ss)}$ | Steady state common-mode out voltage | tput | C at 0 V Figure 0 | 2 | 2.3 | 3 | ٧ |
| $\Delta V_{OC(ss)}$ | Change in steady-state common output voltage | n-mode | S at 0 V, Figure 8 | | 30 | | mV |
| I _{IH} | High-level input current, TXD in | put | V _I at V _{CC} | -2 | | 2 | |
| I _{IL} | Low-level input current, TXD inp | out | V _I at 0 V | – 50 | | -10 | μА |
| $I_{O(off)}$ | Power-off TXD output current | | V _{CC} at 0 V, TXD at 5 V | | | 1 | |
| | | | V _{CANH} = -12 V, CANL open, See Figure 11 | -105 | -72 | | |
| i | Chart aireuit ataadu atata autaut | . OLUMNO 10t | V _{CANH} = 12 V, CANL open, See Figure 11 | | 0.36 | 1 | |
| $I_{OS(ss)}$ | Short-circuit steady-state output current | | V _{CANL} = -12 V, CANH open, See Figure 11 | -1 | -0.5 | | mA |
| | | | V _{CANL} = 12 V, CANH open, See Figure 11 | | 71 | 105 | |
| Co | Output capacitance | | See receiver input capacitance | | | | |

⁽¹⁾ All typical values are at 25°C with a 5-V supply.

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------|--|---------------------------------|-----|-----|-----|------|
| t _{PLH} | Propagation delay time, low-to-high level output | S at 0 V, See Figure 4 | 25 | 65 | 120 | ns |
| t _{PHL} | Propagation delay time, high-to-low level output | S at 0 V, See Figure 4 | 25 | 45 | 120 | ns |
| t _r | Differential output signal rise time | S at 0 V, See Figure 4 | | 25 | | ns |
| t _f | Differential output signal fall time | S at 0 V, See Figure 4 | | 50 | | ns |
| t _{en} | Enable time from silent mode to dominant | See Figure 7 | | | 1 | μS |
| t _(dom) | Dominant time out | ↓V _I , See Figure 10 | 300 | 450 | 700 | μS |



RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|---------------------|---|--|-----|--------------------|-----|------|
| $V_{\text{IT+}}$ | Positive-going input threshold voltage | S at 0 V, See Table 3 | | 800 | 900 | mV |
| $V_{\text{IT-}}$ | Negative-going input threshold voltage | S at 0 V, See Table 3 | 500 | 650 | | mV |
| V_{hys} | Hysteresis voltage $(V_{IT+} - V_{IT-})$ | | 100 | 125 | | mV |
| V_{OH} | High-level output voltage | I _O = -2 mA, See Figure 6 | 4 | 4.6 | | V |
| V_{OL} | Low-level output voltage | I _O = 2 mA, See Figure 6 | | 0.2 | 0.4 | V |
| I _{I(off)} | Power-off bus input current | CANH or CANL = 5 V, Other pin at 0 V, V _{CC} at 0 V, TXD at 0 V | | 165 | 250 | μА |
| $I_{O(off)}$ | Power-off RXD leakage current | V _{CC} at 0 V, RXD at 5 V | | | 20 | μА |
| Cı | Input capacitance to ground (CANH or CANL) | TXD at 3 V, V _I = 0.4 sin (4E6πt) + 2.5 V | | 13 | | pF |
| C_{ID} | Differential input capacitance | TXD at 3 V, $V_1 = 0.4 \sin (4E6\pi t)$ | | 5 | | pF |
| R_{ID} | Differential input resistance | TXD at 3 V, S at 0 V | 30 | | 80 | kΩ |
| R _{IN} | Input resistance (CANH or CANL) | TXD at 3 V, S at 0 V | 15 | 30 | 40 | kΩ |
| R _{I(m)} | Input resistance matching [1 – (R _{IN (CANH)} / R _{IN (CANL)})] × 100% | $V_{(CANH)} = V_{(CANL)}$ | -3 | 0 | 3 | % |

⁽¹⁾ All typical values are at 25°C with a 5-V supply.

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|------------------|--|--|-----|-----|-----|------|
| t _{PLH} | Propagation delay time, low-to-high-level output | | 60 | 100 | 130 | ns |
| t_{PHL} | Propagation delay time, high-to-low-level output | S at 0 V at V Saa Figure 6 | 45 | 70 | 130 | ns |
| t _r | Output signal rise time | S at 0 V or V _{CC} , See Figure 6 | | 8 | | ns |
| t _f | Output signal fall time | | | 8 | | ns |

S PIN CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | | TEST CONDI | TIONS | • | MIN | TYP | MAX | UNIT |
|-----------------|--------------------------|------------|------------|-------|---|-----|-----|-----|------|
| I _{IH} | High level input current | S at 2 V | | | | 20 | 40 | 70 | μА |
| $I_{\rm IL}$ | Low level input current | S at 0.8 V | | | | 5 | 20 | 30 | μА |

VREF PIN CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------|--------------------------|---------------------------------|---------------------|---------------------|--------------|------|
| V_{O} | Reference output voltage | –50 μA < I _O < 50 μA | 0.4 V _{CC} | 0.5 V _{CC} | $0.6 V_{CC}$ | V |



THERMAL CHARACTERISTICS

over recommended operating conditions including operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|--------------------------------------|---|--------|-----|-----|-------|
| 0 | lunation to air thormal registance | Low-K thermal resistance ⁽¹⁾ | | 211 | | °C/W |
| θ_{JA} | Junction-to-air thermal resistance | High-K thermal resistance | | 131 | | -0/00 |
| θ_{JB} | Junction-to-board thermal resistance | | | 53 | | °C/W |
| θ_{JC} | Junction-to-case thermal resistance | | | 79 | | °C/W |
| В | | $\rm V_{CC}=5~V,T_J=27^{\circ}C,R_L=60~\Omega,S$ at 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, CL at RXD = 15 pF | | 112 | | m\\\ |
| P _D | Average power dissipation | $\rm V_{CC}=5.5~V,~T_{J}=130^{\circ}C,~R_{L}=45~\Omega,~S$ at 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, CL at RXD = 15 pF | /e, 17 | | 170 | mW |
| | Thermal shutdown temperature | | | 190 | | °C |

⁽¹⁾ Tested in accordance with the low-K or high-K thermal metric definitions of EIA/JESD51-3 for leaded surface-mount packages.

FUNCTION TABLES

Table 1. DRIVER⁽¹⁾

| INP | UTS | OUTP | BUS STATE | | |
|------|-----------|--------|-----------|-----------|--|
| TXD | S | S CANH | | BOS STATE | |
| L | L or Open | Н | L | Dominant | |
| Н | X | Z | Z | Recessive | |
| Open | X | Z | Z | Recessive | |
| Х | Н | Z Z | | Recessive | |

(1) H = high level, L = low level, X = irrelevant, ? = indeterminate, Z = high impedance

Table 2. RECEIVER⁽¹⁾

| DIFFERENTIAL INPUTS V _{ID} = V(CANH) - V(CANL) | OUTPUT RXD | BUS STATE |
|--|---------------|-----------|
| V _{ID} ≥ 0.9 V | L | Dominant |
| 0.5 V < V _{ID} < 0.9 V | ? | ? |
| V _{ID} ≤ 0.5 V | Н | Recessive |
| Open | Н | Recessive |

(1) H = high level, L = low level, X = irrelevant, ? = indeterminate, Z = high impedance



PARAMETER MEASUREMENT INFORMATION

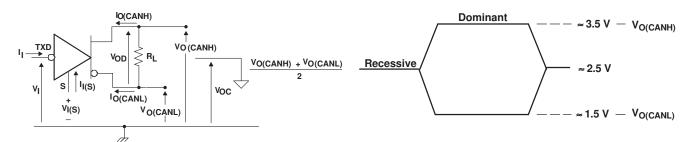


Figure 1. Driver Voltage, Current, and Test Definition

Figure 2. Bus Logic State Voltage Definitions

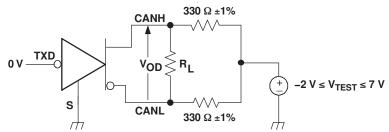


Figure 3. Driver V_{OD} Test Circuit

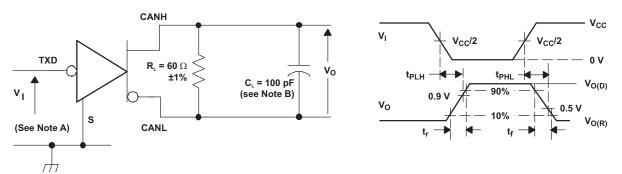


Figure 4. Driver Test Circuit and Voltage Waveforms

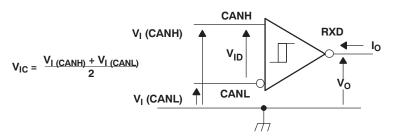
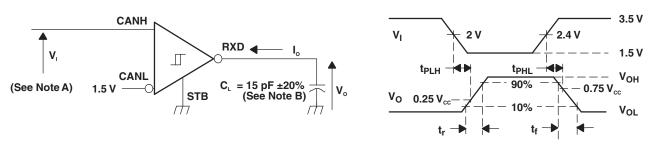


Figure 5. Receiver Voltage and Current Definitions



PARAMETER MEASUREMENT INFORMATION (continued)

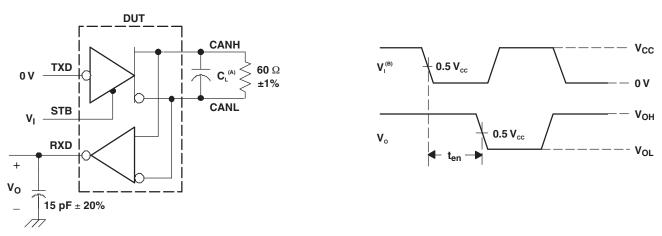


- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 125 kHz, 50% duty cycle, $t_r \leq$ 6 ns, $t_f \leq$ 6 ns, $t_G \leq$ 50 Ω .
- B. C_L includes instrumentation and fixture capacitance within ±20%.

Figure 6. Receiver Test Circuit and Voltage Waveforms

Table 3. Differential Input Voltage Threshold Test

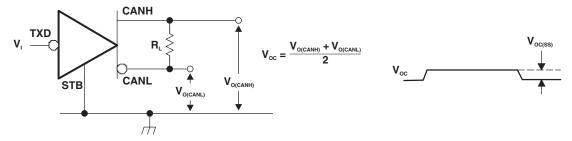
| | INPUT | | OUTPUT | |
|-------------------|-------------------|-----------------|--------|-----------------|
| V _{CANH} | V _{CANL} | V _{ID} | | R |
| –11.1 V | –12 V | 900 mV | L | |
| 12 V | 11.1 V | 900 mV | L | |
| −6 V | -12 V | 6 V | L | V _{OL} |
| 12 V | 6 V | 6 V | L | |
| –11.5 V | -12 V | 500 mV | Н | |
| 12 V | 11.5 V | 500 mV | Н | |
| -12 V | -6 V | 6 V | Н | V _{OH} |
| 6 V | 12 V | 6 V | Н | 1 |
| Open | Open | X | Н | 1 |



- A. $C_L = 100 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.
- B. All V_1 input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

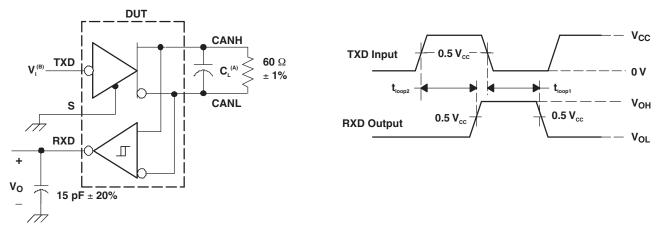
Figure 7. t_{en} Test Circuit and Waveforms





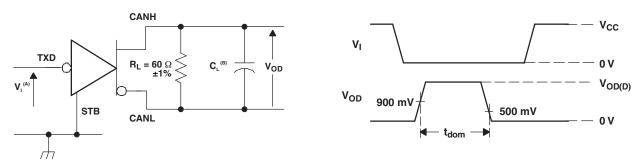
NOTE: All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

Figure 8. Common-Mode Output Voltage Test and Waveforms



- A. C_L = 100 pF and includes instrumentation and fixture capacitance within ±20%.
- B. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

Figure 9. t_(LOOP) Test Circuit and Waveforms



- A. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 500 Hz, 50% duty cycle.
- B. $C_1 = 100 \text{ pF}$ includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 10. Dominant Time-Out Test Circuit and Waveforms



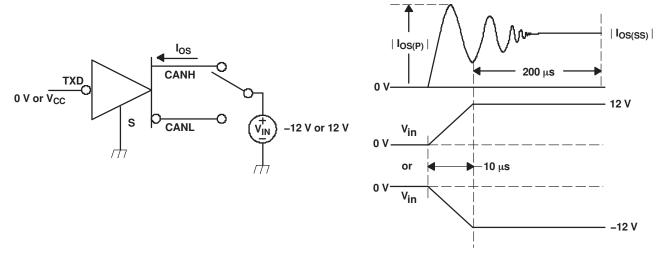
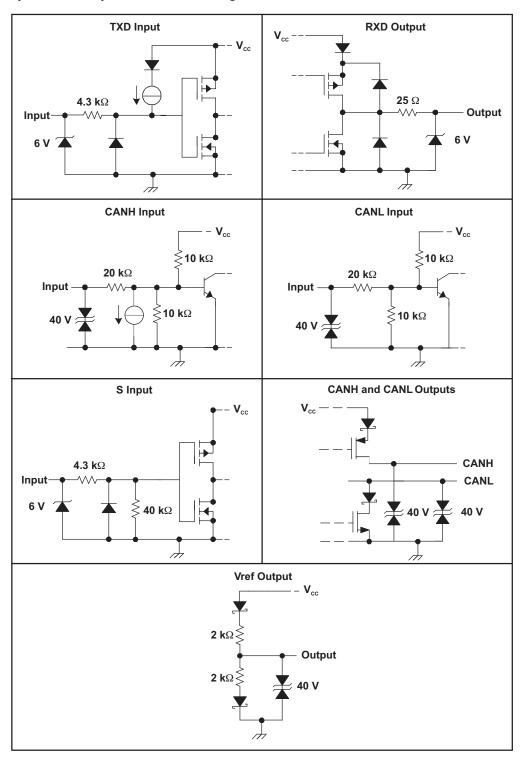


Figure 11. Driver Short-Circuit Current Test and Waveforms



Equivalent Input and Output Schematic Diagrams





PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|--------------|-------------------------------|--------------------|--------------|----------------------|---------|
| | | | | | | | (6) | | | | |
| SN65HVD1050QDRQ1 | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | H1050Q | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN65HVD1050-Q1:



PACKAGE OPTION ADDENDUM

10-Dec-2020

Catalog: SN65HVD1050

• Enhanced Product: SN65HVD1050-EP

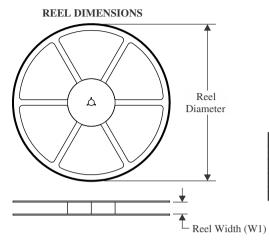
NOTE: Qualified Version Definitions:

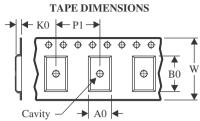
- Catalog TI's standard catalog product
- Enhanced Product Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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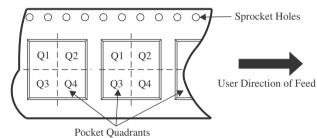
TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width |
|----|---|
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

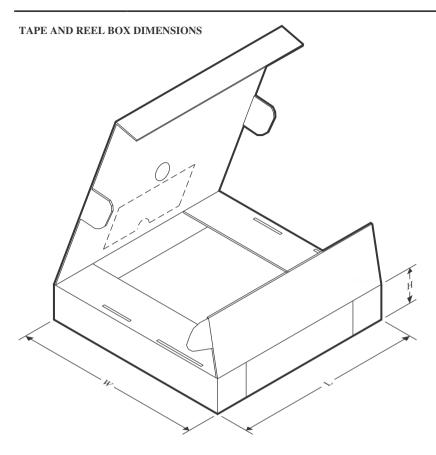


*All dimensions are nominal

| Device | • | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|------------------|------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN65HVD1050QDRQ1 | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

| | Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|------------------|--------------|-----------------|------|------|-------------|------------|-------------|
| I | SN65HVD1050QDRQ1 | SOIC | D | 8 | 2500 | 356.0 | 356.0 | 35.0 |

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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